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CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

1N3600
1N4150

SILICON SWITCHING DIODE

JEDEC DO-35 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 1N3600, 1N4150, silicon planar epitaxial diode is characterized by its miniature size, ultra fast switching speed, low capacitance, low leakage, and high conductance. Accordingly, it is ideally suited for applications such as pulse applications, avalanche circuits, core drivers, and for any critical circuit requiring high conductance at power dissipation without sacrificing fast recovery capability. (Both devices have identical electrical and mechanical specifications).

MAXIMUM RATINGS (T_A=25°C)

| | SYMBOL | | UNIT |
|--|-----------------------------------|-------------|------|
| Peak Working Inverse Voltage | V _{RWM} | 50 | V |
| Average Forward Current | I _O | 200 | mA |
| Forward Steady State Current | I _F | 400 | mA |
| Recurrent Peak Forward Current | i _f | 600 | mA |
| Peak Forward Surge Current (1.0s Pulse) | I _{FSM} | 1.0 | A |
| Peak Forward Surge Current (1.0μs Pulse) | I _{FSM} | 4.0 | A |
| Power Dissipation | P _D | 500 | mW |
| Operating and Storage | | | |
| Junction Temperature | T _J , T _{STG} | -65 to +200 | °C |

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

| SYMBOL | TEST CONDITIONS | MIN | MAX | UNIT |
|-----------------|--|------|------|------|
| I _R | V _R =Rated V _{RWM} | | 100 | nA |
| I _R | V _R =Rated V _{RWM} , T _A =150°C | | 100 | μA |
| BV _R | I _R =5.0μA | 75 | | V |
| V _F | I _F =1.0mA | 0.54 | 0.62 | V |
| V _F | I _F =10mA | 0.66 | 0.74 | V |
| V _F | I _F =50mA | 0.76 | 0.86 | V |
| V _F | I _F =100mA | 0.82 | 0.92 | V |
| V _F | I _F =200mA | 0.87 | 1.0 | V |
| C | V _R =0V, f=1.0MHz | | 2.5 | pF |
| t _{fr} | V _{fr} =1.0V, I _F =200mA, t _r =0.4ns | | 10 | ns |
| t _{rr} | I _F =I _R =10mA to 200mA, R _L =100Ω | | 4.0 | ns |
| t _{rr} | I _F =I _R =200mA to 400mA, R _L =100Ω | | 6.0 | ns |

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- PbSn plating options
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- Application notes
- Application and design sample kits
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